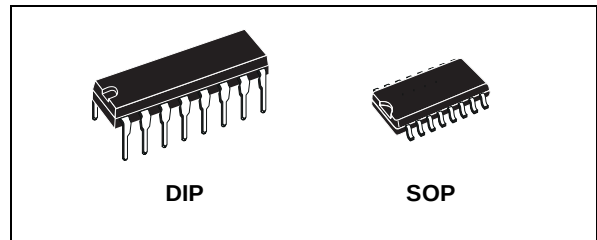


HEX BUFFER/CONVERTER (NON INVERTING)

- PROPAGATION DELAY TIME :
 $t_{PD} = 40\text{ns}$ (TYP.) at $V_{DD} = 10\text{V}$ $C_L = 50\text{pF}$
- HIGH TO LOW LEVEL LOGIC CONVERSION
- HIGH "SINK" AND "SOURCE" CURRENT CAPABILITY
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT
 $I_I = 100\text{nA}$ (MAX) AT $V_{DD} = 18\text{V}$ $T_A = 25^\circ\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



ORDER CODES

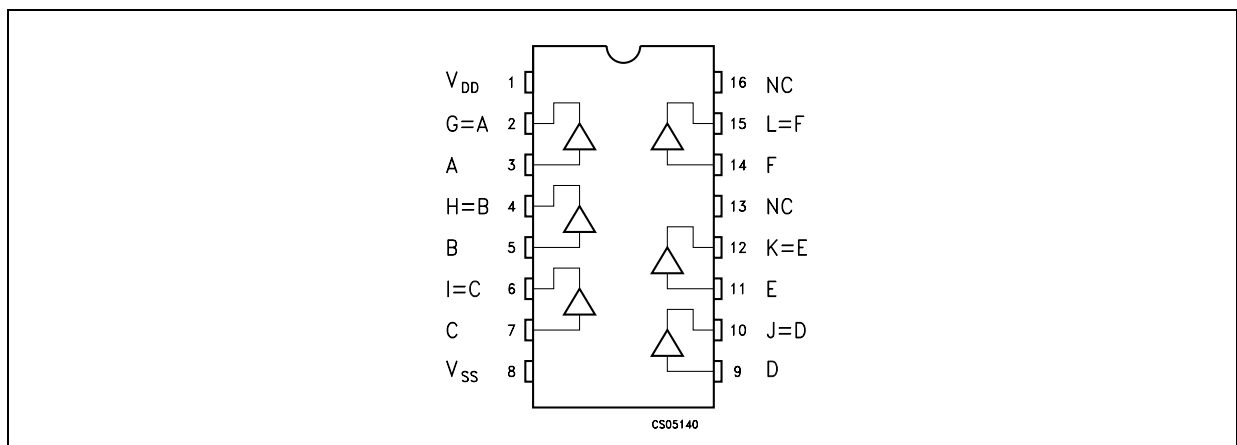
PACKAGE	TUBE	T & R
DIP	HCF4050BEY	
SOP	HCF4050BM1	HCF4050M013TR

DESCRIPTION

The HCF4050B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. It is an non inverting Hex Buffer/Converter and feature logic level conversions using only one supply voltage (V_{DD}).

The input high level signal (V_{IH}) can exceed the V_{DD} supply voltage when these devices are used for logic level conversions. This device is intended for use as CMOS to DTL/TTL converters and can drive directly two DTL/TTL loads ($V_{DD}=5\text{V}$, $V_{OL}\leq 0.4\text{V}$ and $I_{OL}\leq 3.2\text{mA}$).

PIN CONNECTION



DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value							Unit
		V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _A = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
I _L	Quiescent Current	0/5			5		0.02	1		30		30	μA
		0/10			10		0.02	2		60		60	
		0/15			15		0.02	4		120		120	
		0/20			20		0.04	20		600		600	
V _{OH}	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V _{OL}	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V _{IH}	High Level Input Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
V _{IL}	Low Level Input Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
I _{OH}	Output Drive Current	0/5	2.5	<1	5	-1.25	-6.4		-0.42		-0.42		mA
		0/5	4.6	<1	5	-0.51	-1.6		-0.38		-0.38		
		0/10	9.5	<1	10	-1.25	-3.6		-1		-1		
		0/15	13.5	<1	15	-3.75	-12		-3		-3		
I _{OL}	Output Sink Current	0/5	0.4	<1	5	3.2	6.4		2.6		2.6		mA
		0/10	0.5	<1	10	8	16		6.6		6.6		
		0/15	1.5	<1	15	24	48		19		19		
I _I	Input Leakage Current	0/18	Any Input		18		±10 ⁻⁵	±0.1		±1		±1	μA
C _I	Input Capacitance		Any Input				5	7.5					pF

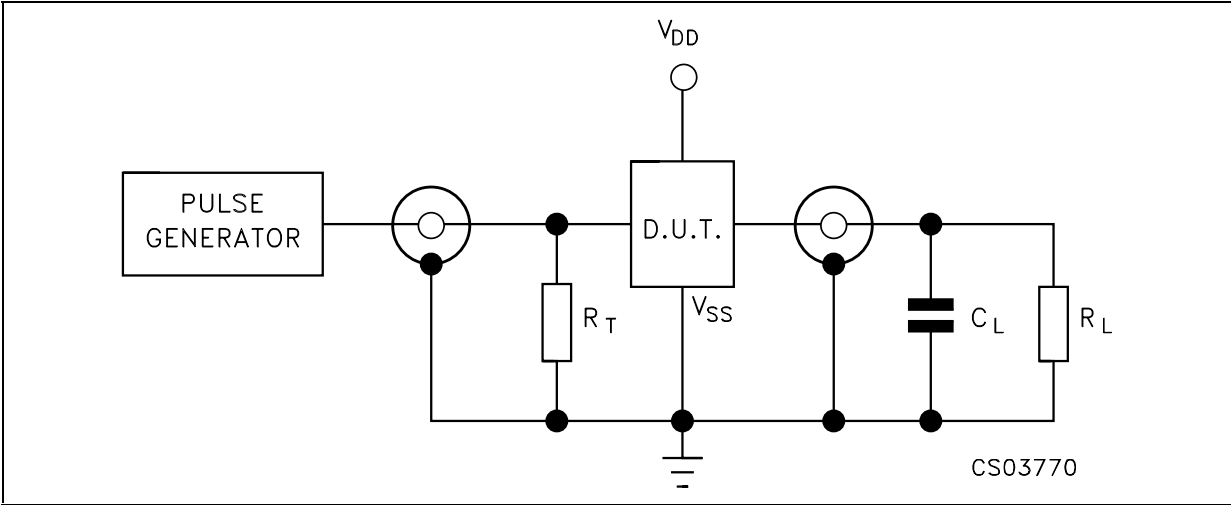
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}=5V, 2V min. with V_{DD}=10V, 2.5V min. with V_{DD}=15V

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200KΩ, t_r = t_f = 20 ns)

Symbol	Parameter	Test Condition			Value (*)			Unit
		V _{DD} (V)	V _I (V)		Min.	Typ.	Max.	
t _{TLH}	Output Transition Time	5	5			80	160	ns
		10	10			40	80	
		15	15			30	60	
t _{THL}	Output Transition Time	5	5			30	60	ns
		10	10			20	40	
		15	15			15	30	
t _{PLH}	Propagation Delay Time	5	5			70	140	ns
		10	10			40	80	
		5	10			45	90	
		15	15			30	60	
		5	15			40	80	
t _{PHL}	Propagation Delay Time	5	5			55	110	ns
		10	10			22	55	
		5	10			50	100	
		15	15			15	30	
		5	15			50	100	

(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

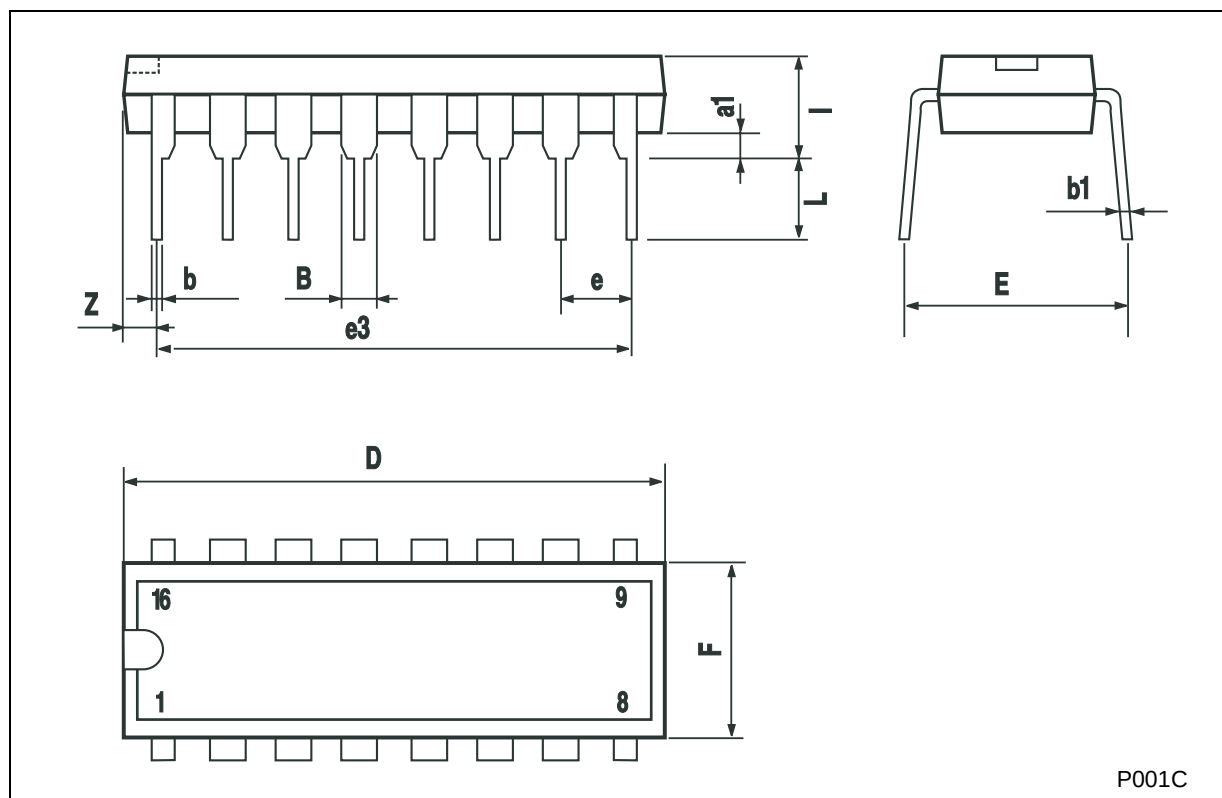
TEST CIRCUIT



C_L = 50pF or equivalent (includes jig and probe capacitance)
R_L = 200KΩ
R_T = Z_{OUT} of pulse generator (typically 50Ω)

Plastic DIP-16 (0.25) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C